

# FRD MODULE 100A/1200V/trr:250nsec

# PD100F12

OUTLINE DRAWING

# FEATURES

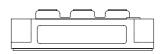
- \* Isolated Base
- \* Dual Diode Doubler Circuit
- \* Ultra Fast Recovery
- \* High Surge Capability
- \* UL Recognized, File No. E187184

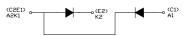
Maximum Ratings

## TYPICAL APPLICATIONS

\* High Frequency Rectification

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## Approx Net Weight:210g

Voltage Rating	Symbol	PD100F12		Unit
Repetitive Peak Reverse Voltage per Arm	Vrrm	1200		V
Electrical Rating		Condition	Rating	
Average Rectified Output Current	Io	50Hz Half Sine Wave condition per Arm Tc=60°C	100	А
RMS Forward Current	IF(RMS)	per Arm	157	А
Surge Forward Current	ECM (	50 Hz Half Sine Wave,1cycle Non-repetitive per Arm	1000	А
I Squared t	I²t	2 msec to 10 msec per Arm	5000	A <sup>2</sup> s
Operating JunctionTemperature Range	Tjw		-40 to +150	°C
Storage Temperature Range	Tstg		-40 to +125	°C
Isoration Voltage	Viso	Base Plate to Terminal, AC1min	2500	V
Mounting torque	Ftor	Case mounting(recommended)	2.8	N•m
		Terminal Screw(recommended)	2.8	

## Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Max.	Unit	
Peak Forward Voltage	VFM	I <sub>FM</sub> = 100A, Tj=25°C, per Arm	2.60	V	
Peak Reverse Current	I <sub>RM</sub>	V <sub>RM</sub> = V <sub>RRM</sub> , Tj= 150°C, per Arm	20	mA	
Reverse Recovery Time	trr	I <sub>FM</sub> = 10A, -di/dt= 50 A/µs, Ta= 25°C Per Arm	250	ns	
Thermal Resistance	Rth(j-c)	Junction to Case per Arm	0.28	°C/W	
	Rth(c-f)	Base Plate to Heat Sink with Thermal Compound	0.1		
Internal Lead Inductance	Ls	Anode Terminal to Cathode Terminal Per Element	30	nH	



# PD100F12 OUTLINE DRAWING (Dimensions in mm)

